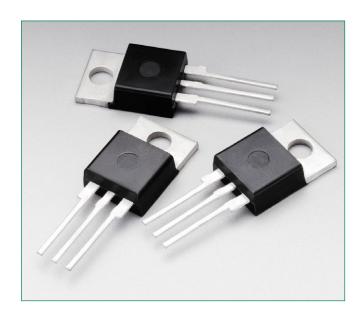


# MAC12D, MAC12M, MAC12N





#### **Description**

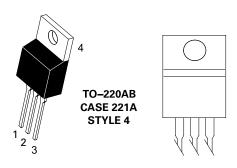
Designed for high performance full—wave ac control applications where high noise immunity and commutating di/dt are required.

# **Features**

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 70°C
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Immunity to dv/dt

   250 V/µs Minimum at
   125°C
- High Commutating di/ dt – 6.5 A/ms Minimum at 125°C
- Industry Standard TO-220 Package
- High Surge Current Capability – 100 Amperes
- These Devices are Pb–Free and are RoHS Compliant

#### **Pin Out**



#### **Functional Diagram**



#### **Additional Information**









# Maximum Ratings (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_{_{\rm J}}$ = -25° to 100°C)	MAC12D MAC12M MAC12N	V <sub>DRM</sub> ,	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 70°C)	I <sub>T (RMS)</sub>	10	А	
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>c</sub> = 125°C)		I <sub>TSM</sub>	100	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	41	A²sec	
Peak Gate Power (Pulse Width ≤ 1.0 µs, T <sub>C</sub> = 80°C)	P <sub>GM</sub>	16	W	
Average Gate Power (t = 8.3 ms, $T_c = 80$ °C)	P <sub>G(AV)</sub>	0.35	W	
Operating Junction Temperature Range	T <sub>J</sub>	-40 to +125	°C	
Storage Temperature Range		T <sub>stg</sub>	-40 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied.

#### **Thermal Characteristics**

Rating	Symbol	Value	Unit	
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		$T_{L}$	260	°C

#### Electrical Characteristics - OFF (T, = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	0.01	m ^
$(V_D = V_{DRM} = V_{RRM})$ ; Gate Open)	$T_{J}^{\circ} = 125^{\circ}C$	I <sub>RRM</sub>	-	-	2.0	mA

#### Electrical Characteristics - ON (T<sub>1</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) ( $I_{TM} = \pm 11 \text{ A}$ )		V <sub>TM</sub>	_	1.2	1.6	V
Gate Trigger Current	MT2(+), G(+)		5.0	13	35	
(Continuous dc)	MT2(+), G(-)	l <sub>GT</sub>	5.0	13	35	mA
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)		5.0	13	35	
Holding Current ( $V_D = 12 \text{ V}$ , Gate Open, Initiating Current = $\pm 150 \text{ mA}$ ))		I <sub>H</sub>	-	30	40	mA
	MT2(+), G(+)	I <sub>L</sub>	_	20	50	mA
Latching Current $(V_D = 24 \text{ V, } I_C = 50 \text{ mA})$	MT2(+), G(-)		_	30	80	
(* <sub>D</sub> = 2 · *, r <sub>G</sub> = 33 · m ·)	MT2(-), G(-)		_	20	50	
MT2(+), G(+)			0.5	0.78	1.5	
Gate Trigger Voltage $(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(+), G(-)	V <sub>GT</sub>	0.5	0.70	1.5	V
(1 <sub>D</sub> 12 ), (1 <sub>L</sub> 100 11)	MT2(-), G(-)		0.5	0.71	1.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



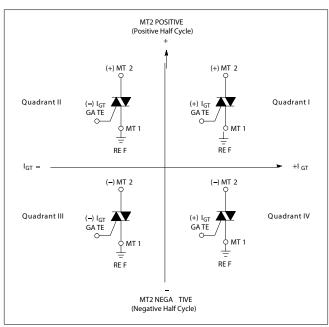
# **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current See Figure 10. $(V_D = 400 \text{ V}, I_{TM} = 4.4 \text{ A}, \text{ Commutating dv/dt} = 18 \text{ V/µs, Gate Open, T}_J = 125 ^{\circ}\text{C}, f = 250 \text{ Hz, No Snubber) } C_L = 10 \text{ µF L}_L = 40 \text{ mH}$	dV/dt	6.5	-	_	A/ms
Critical Rate of Rise of Off-State Voltage ( $V_D = Rated V_{DRM'}$ Exponential Waveform, $R_{GK} = 510 \Omega$ , $T_J = 125$ °C)	dV/dt	500	-	-	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 200 mA/µsec; f = 60 Hz	di/dt	-	-	10	A/µs

# **Voltage Current Characteristic of SCR**

Symbol	Parameter		
$V_{DRM}$	Peak Repetitive Forward Off State Voltage		
I <sub>DRM</sub>	Peak Forward Blocking Current		
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage		
I <sub>RRM</sub>	Peak Reverse Blocking Current		
V <sub>TM</sub>	Maximum On State Voltage		
I <sub>H</sub>	Holding Current		

#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

 $\dot{\text{With}}$  in—phase signals (using standard AC lines) quadrants I and III are used

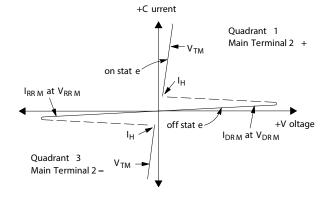




Figure 1. Typical Gate Trigger Current vs Junction Temperature

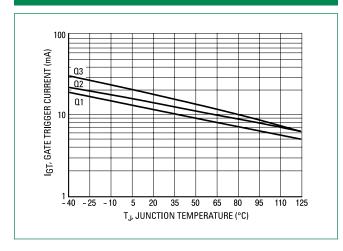
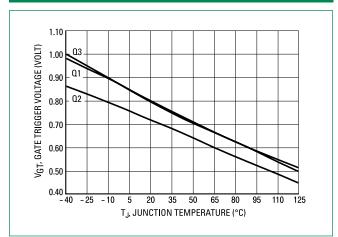


Figure 2. Typical Gate Trigger Voltage vs Junction Temperature



**Figure 3. Typical Holding Current vs Junction Temperature** 

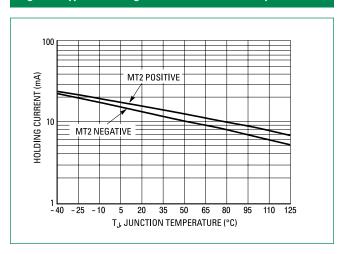
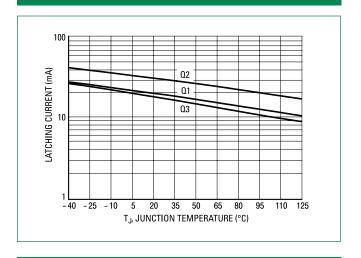


Figure 4. Typical Latching Current vs Junction Temperature



**Figure 5. Typical RMS Current Derating** 

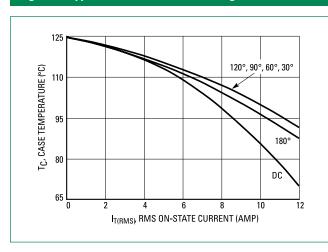
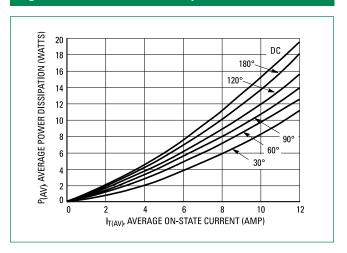
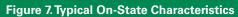


Figure 6. On-State Power Dissipation







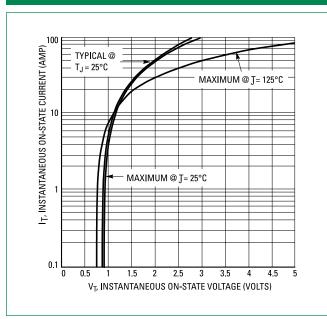
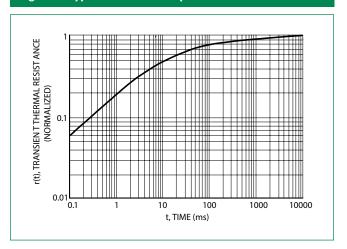
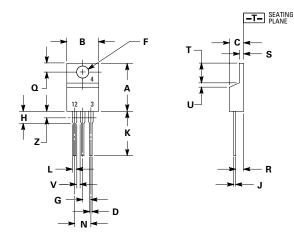


Figure 8. Typical Thermal Response



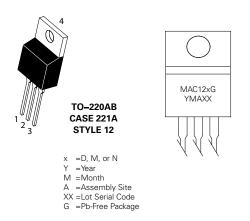


#### **Dimensions**



# **Part Marking System**

**Ordering Information** 



	Inches		Millin	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	No Connection			

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Device	Package	Shipping
MAC12DG		
MAC12MG	TO-220AB (Pb-Free)	500 Units / Rail
MAC12NG	(, , , , , , , , , , , , , , , , , , ,	

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.